

General Description

The WSP4953A is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSP4953A meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

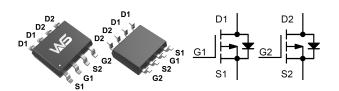
Product Summery

BVDSS	RDSON	ID
-20V	40mΩ	-5.8A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	-20	V	
V_{GS}	Gate-Source Voltage	±12	V	
I _D @T _C =25℃	Continuous Drain Current, -V _{GS} @ -10V ¹	-5.8	Α	
I _D @T _C =100℃	Continuous Drain Current, -V _{GS} @ -10V ¹	-4.6	Α	
I _{DM}	Pulsed Drain Current ²	-20	А	
P _D @T _C =25°C	Total Power Dissipation ³	2.0	W	
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$	
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}$	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		62.5	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		36	°C/W





Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0V , I_D =-250uA	-20			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25°C , I _D =-1mA		-0.02		V/℃
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-5.8A		40	55	mΩ
		V _{GS} =-4.5V , I _D =-3.5A		60	85	
$V_{GS(th)}$	Gate Threshold Voltage	─_V _{GS} =V _{DS} , I _D =-250uA	-1.0	-1.5	-2.0	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient			4.32		mV/℃
	Danier Course I a cleane Course	V_{DS} =-16V , V_{GS} =0V , T_J =25 $^{\circ}$ C			-1	- uA
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-16V , V_{GS} =0V , T_J =55 $^{\circ}$ C			-5	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V_{DS} =-5 V , I_{D} =-3 A		5.5		S
R_g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		24	48	Ω
Q_g	Total Gate Charge (-4.5V)	V _{DS} =-16V , V _{GS} =-4.5V , I _D =-5.8A		11.6	16	
Q_{gs}	Gate-Source Charge			1.3		nC
Q_{gd}	Gate-Drain Charge			2.5		
T _{d(on)}	Turn-On Delay Time			6	12	
Tr	Rise Time	V_{DD} =-15V , V_{GS} =-10V , R_G =6 Ω		12	23	ns
T _{d(off)}	Turn-Off Delay Time	I _D =-1A, RG=10Ω		25	46	
T _f	Fall Time			6	12	
C _{iss}	Input Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		625		
C _{oss}	Output Capacitance			100		pF
C _{rss}	Reverse Transfer Capacitance			60		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}	V _G =V _D =0V , Force Current			-2.0	Α
I _{SM}	Pulsed Source Current ^{2,4}	V _G -V _D -UV , Force Current			-20	Α
V_{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1.7A , T _J =25℃			-1	V

Note:

^{1.} The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.

^{2.}The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%

^{3.}The power dissipation is limited by 150 $^{\circ}\mathrm{C}$ junction temperature

^{4.} The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

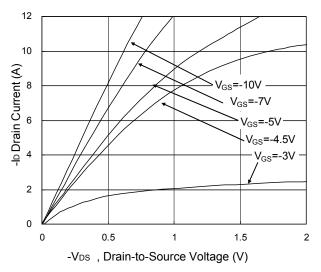


Fig.1 Typical Output Characteristics

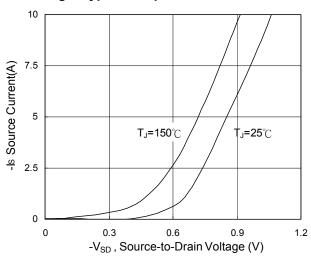


Fig.3 Forward Characteristics of Reverse

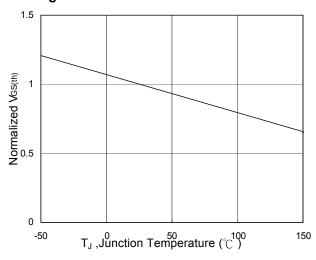


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

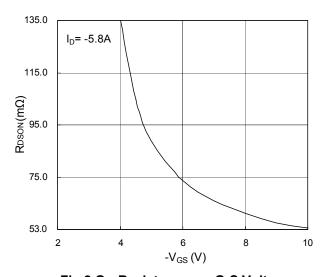


Fig.2 On-Resistance vs. G-S Voltage

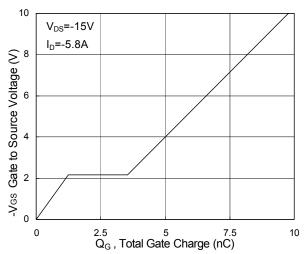


Fig.4 Gate-Charge Characteristics

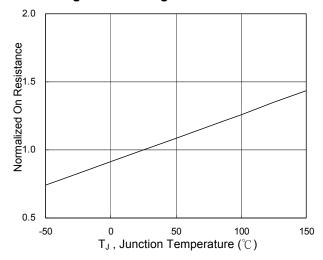
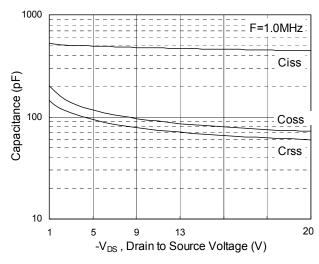


Fig.6 Normalized R_{DSON} vs. T_J





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Fig.7 Capacitance

Fig.8 Safe Operating Area

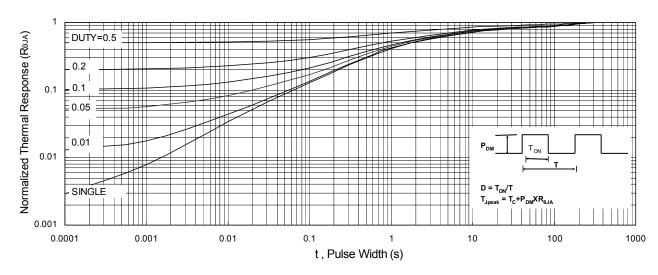
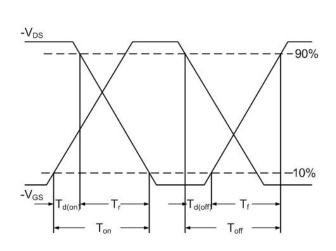


Fig.9 Normalized Maximum Transient Thermal Impedance



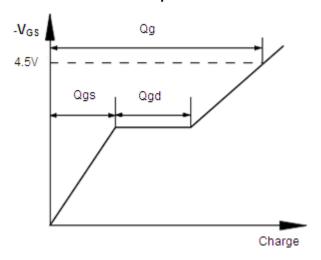


Fig.10 Switching Time Waveform

Fig.11 Gate Charge Waveform



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